

SBR10150CT SBR10150CTF SBR10150CTI SBR10150CTB

## Super Barrier Rectifier TM

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

## Major ratings and characteristics

Characteristics	Values	Units
I <sub>F(AV)</sub> Rectangular Waveform	10	Α
$V_{RRM}$	150	٧
V <sub>F</sub> @5A, Tj=125℃	0.69	V, typ
Tj(operating/storage)	-65 to 150	$^{\circ}\mathbb{C}$

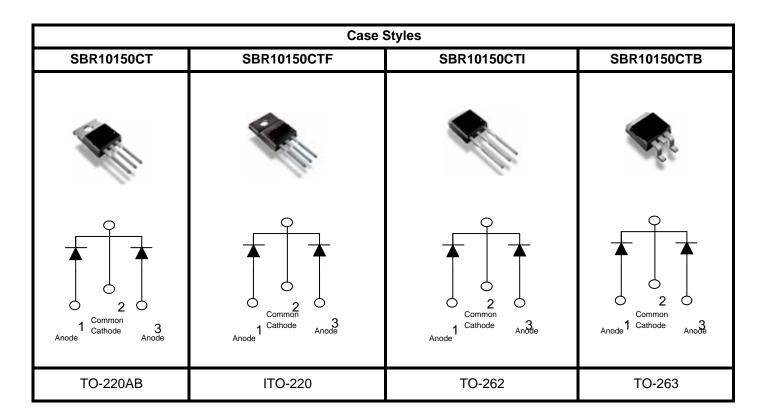
Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications

## **ELECTRICAL**:

- \* Ultra-Low Forward Voltage Drop
- \* Reliable High Temperature Operation
- \* Super Barrier Design
- \* Softest, fast switching capability
- \* 150°C Operating Junction Temperature

## MECHANICAL:

\* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages





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	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V <sub>RM</sub> V <sub>RWM</sub> V <sub>RRM</sub>	150		Volts
Average Rectified Forward Current (Rated V <sub>R</sub> -20Khz Square Wave) - 50% duty cycle	Io	10		Amps
Peak Forward Surge Current - 1/2 60hz	I <sub>FSM</sub>	120		Amps
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I <sub>RRM</sub>	2		Amps
Instantaneous Forward Voltage (per leg) $I_F = 5A; T_J = 25^{\circ}C$ $I_F = 5A; T_J = 125^{\circ}C$	V <sub>F</sub> .	Typ  	Max 0.88 0.79	Volts
Maximum Instantaneous Reverse Current at Rated $V_{RM}$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I <sub>R</sub>	Typ  	Max 0.2 25	mA
Maximum Rate of Voltage Change (at Rated $V_R$ )	dv/dt	10,000		V/uS
Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263 Package = ITO-220	R⊕ <sub>JC</sub>	2 4		°C/W
Operating and Storage Junction Temperature	T₃	-65 to +150		°C

 $<sup>^{\</sup>star}$  Pulse width < 300 uS, Duty cycle < 2%

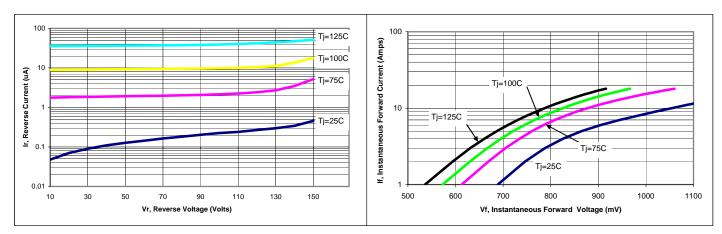


Figure 1: Typical Reverse Current (per leg)

Figure 2: Typical Forward Voltage (per leg)

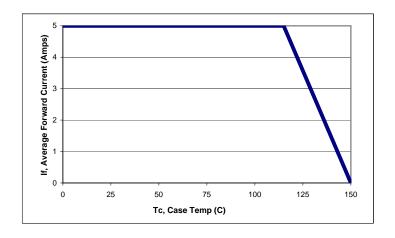


Figure 3: Current Derating, Case (per leg)

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